1S920• 1S921• 1S922• 1S923

GENERAL PURPOSE DIODES

DIFFUSED SILICON PLANAR

- **V_F . . . 1.2 (MAX) @ 200 mA**
- **I_R . . . 100 nA (MAX) @ RATED WIV**

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature Range	−65°C to +200°C
Maximum Junction Operating Temperature	+175°C
Lead Temperature	+260°C

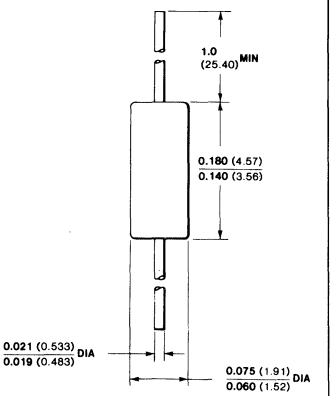
Power Dissipation (Note 2)

Maximum Total Dissipation at 25°C Ambient	500 mW
Linear Derating Factor (from 25°C)	3.33 mW/°C

Maximum Voltage and Currents

		1S920	1S921	1S922	1S923
WIV	Working Inverse Voltage (−65°C to +100°C)	50 V	100 V	150 V	200 V
I_O	Average Forward Current	200 mA	200 mA	200 mA	200 mA
i_f	Recurent Peak Forward Current	600 mA	600 mA	600 mA	600 mA
$i_{f(surge)}$	Peak Forward Surge Current				
	Pulse Width = 1 s	1.0 A	1.0 A	1.0 A	1.0 A
	Pulse Width = 1 μs	4.0 A	4.0 A	4.0 A	4.0 A

DO-35 OUTLINE



NOTES:
Copper clad steel leads, tin plated
Gold plated leads available
Hermetically sealed glass package
Package weight is 0.14 gram

ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
I_R	Inverse Current		100 10	nA μA	V_R = rated WIV V_R = rated WIV, T_A = 100°C
V_F	Forward Voltage		1.2	V	I_F = 200 mA
C	Capacitance		6.5	pF	V_R = 0, f = 1 MHz
Q_S	Stored Charge		12	nC	I_F = 10 mA, V_R = 10 V

NOTES:
1. These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
3. For product family characteristic curves, refer to Chapter 4, D1.